

1SS286

FEATURES :

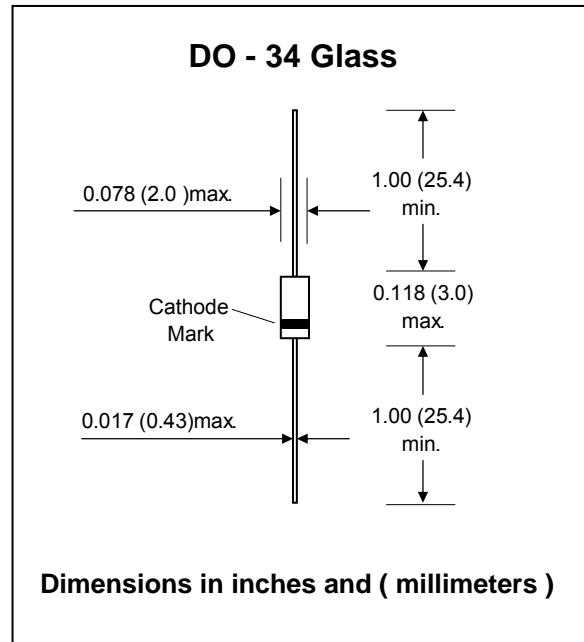
- Very Low I_{R}
- Low V_F and high efficiency.
- Pb / RoHS Free

MECHANICAL DATA :

Case: DO-34 Glass Case

Weight: approx. 0.11g

SCHOTTKY BARRIER DIODE



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified)

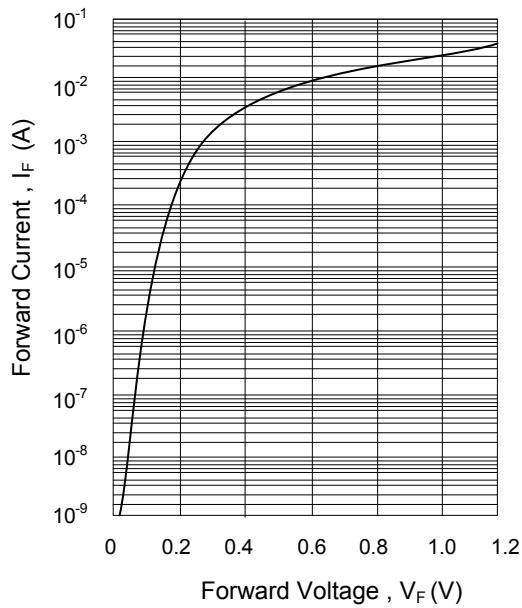
Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	25	V
Average Rectified Current	I_o	35	mA
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	100	°C
Storage temperature range	T_{stg}	-55 to + 100	°C

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

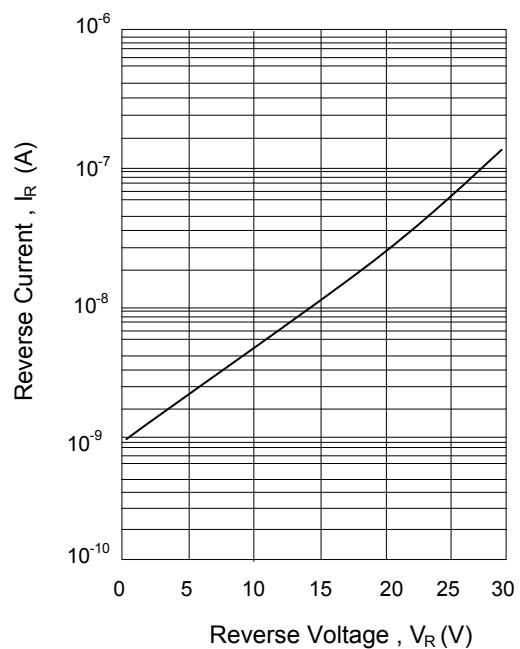
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	I_R	$V_R = 10 \text{ V}$	-	-	10	nA
Reverse Voltage	V_R	$I_R = 10 \mu\text{A}$	25	-	-	V
Forward Voltage	V_F	$I_F = 10 \text{ mA}$	-	-	0.6	V
Forward Current	I_F	$V_F = 1 \text{ V}$	3.0	-	-	mA
Diode Capacitance	C_d	$V_R = 0\text{V}, f = 1\text{MHz}$	-	-	1.2	pF
Diode Capacitance Deviation	ΔC_d	$V_R = 0\text{V}, f = 1\text{MHz}$	-	-	± 0.05	pF
Forward Voltage Deviation	ΔV_F	$I_F = 10 \text{ mA}$	-	-	± 5	mV

RATING AND CHARACTERISTIC CURVES (1SS286)

Forward Current VS. Forward Voltage



Reverse Current VS. Reverse Voltage



Diode capacitance VS. Reverse Voltage

